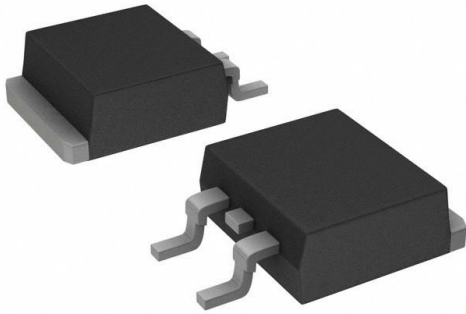


FQB17N08TM Datasheet

www.digi-electronics.com



DiGi Electronics Part Number	FQB17N08TM-DG
Manufacturer	onsemi
Manufacturer Product Number	FQB17N08TM
Description	MOSFET N-CH 80V 16.5A D2PAK
Detailed Description	N-Channel 80 V 16.5A (Tc) 3.13W (Ta), 65W (Tc) Surface Mount TO-263 (D2PAK)

<https://www.DiGi-Electronics.com>



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

FQB17N08TM

Series:

QFET®

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

80 V

Drive Voltage (Max Rds On, Min Rds On):

10V

Vgs(th) (Max) @ Id:

4V @ 250µA

Vgs (Max):

±25V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

TO-263 (D2PAK)

Base Product Number:

FQB1

Manufacturer:

onsemi

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

16.5A (Tc)

Rds On (Max) @ Id, Vgs:

115mOhm @ 8.25A, 10V

Gate Charge (Qg) (Max) @ Vgs:

15 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

450 pF @ 25 V

Power Dissipation (Max):

3.13W (Ta), 65W (Tc)

Mounting Type:

Surface Mount

Package / Case:

TO-263-3, D2PAK (2 Leads + Tab), TO-263AB

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095



January 2001

QFET™

FQB17N08 / FQI17N08

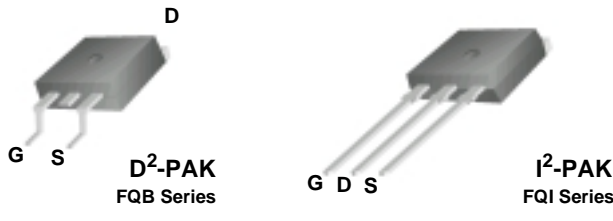
80V N-Channel MOSFET

General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand a high energy pulse in the avalanche and commutation modes. These devices are well suited for low voltage applications such as automotive, high efficiency switching for DC/DC converters, and DC motor control.

Features

- 16.5A, 80V, $R_{DS(on)} = 0.115\Omega @ V_{GS} = 10 V$
- Low gate charge (typical 12 nC)
- Low Crss (typical 28 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FQB17N08 / FQI17N08	Units
V _{DSS}	Drain-Source Voltage	80	V
I _D	Drain Current - Continuous (T _C = 25°C)	16.5	A
	- Continuous (T _C = 100°C)	11.6	A
I _{DM}	Drain Current - Pulsed (Note 1)	66	A
V _{GSS}	Gate-Source Voltage	± 25	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	100	mJ
I _{AR}	Avalanche Current (Note 1)	16.5	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	6.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.5	V/ns
P _D	Power Dissipation (T _A = 25°C) *	3.13	W
	Power Dissipation (T _C = 25°C)	65	W
	- Derate above 25°C	0.43	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	--	2.31	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient *	--	40	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	80	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.08	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 64\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 8.25\text{ A}$	--	0.088	0.115	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 30\text{ V}, I_D = 8.25\text{ A}$ (Note 4)	--	5.3	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	350	450	pF
C_{oss}	Output Capacitance		--	120	155	pF
C_{riss}	Reverse Transfer Capacitance		--	28	35	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 40\text{ V}, I_D = 16.5\text{ A},$ $R_G = 25\ \Omega$	--	4.8	20	ns	
t_r	Turn-On Rise Time		--	60	130	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4, 5)	--	15	40	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	25	60	ns
Q_g	Total Gate Charge	$V_{DS} = 64\text{ V}, I_D = 16.5\text{ A},$ $V_{GS} = 10\text{ V}$	--	12	15	nC	
Q_{gs}	Gate-Source Charge		(Note 4, 5)	--	2.7	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	5.4	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	16.5	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	66	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 16.5\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 16.5\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	55	--	ns
Q_{rr}	Reverse Recovery Charge		--	92	--	nC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 0.5\text{ mH}, I_{AS} = 16.5\text{ A}, V_{DD} = 25\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 16.5\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

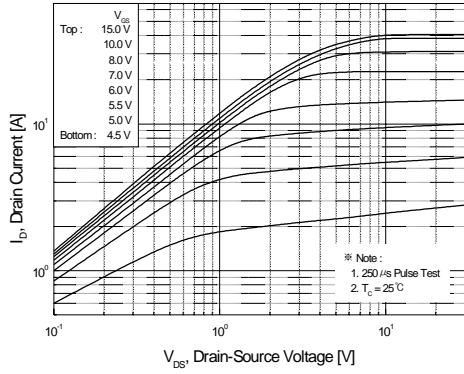


Figure 1. On-Region Characteristics

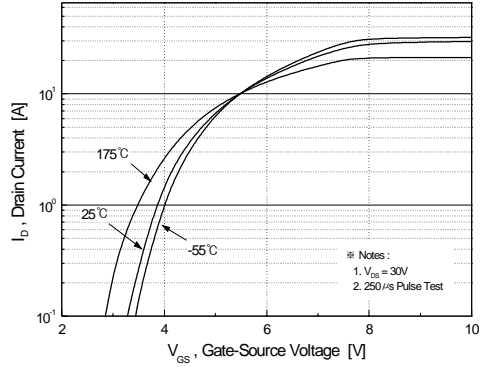


Figure 2. Transfer Characteristics

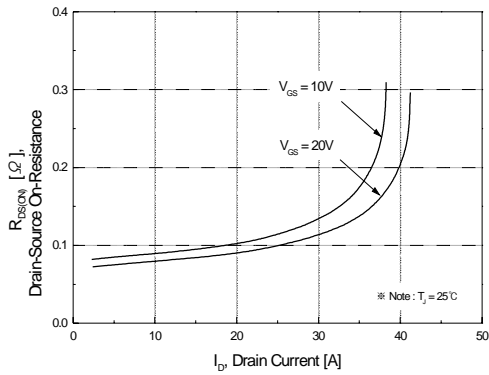


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

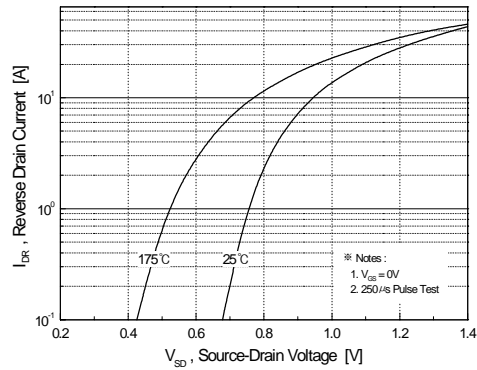


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

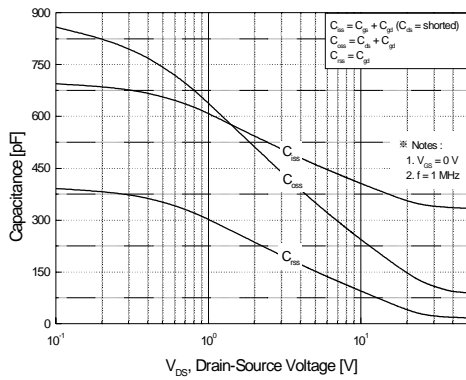


Figure 5. Capacitance Characteristics

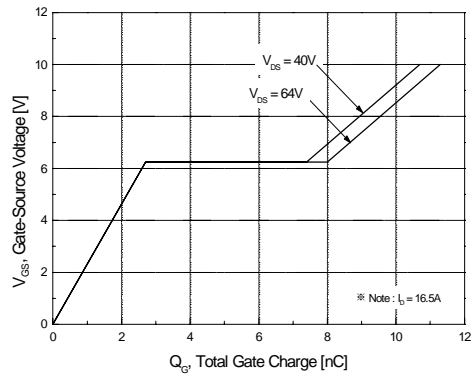


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

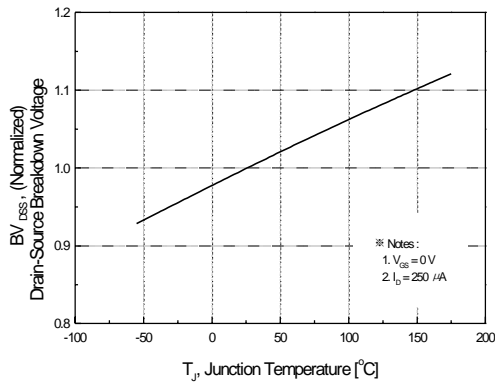


Figure 7. Breakdown Voltage Variation vs. Temperature

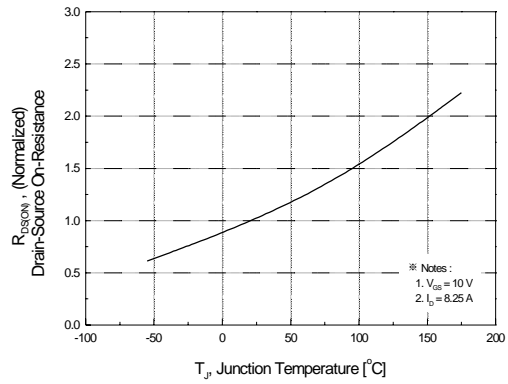


Figure 8. On-Resistance Variation vs. Temperature

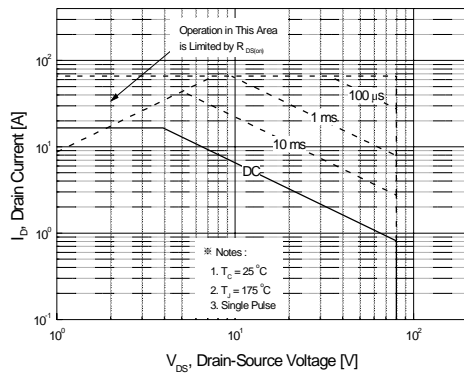


Figure 9. Maximum Safe Operating Area

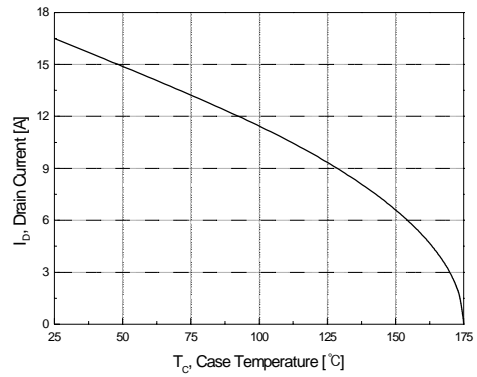


Figure 10. Maximum Drain Current vs. Case Temperature

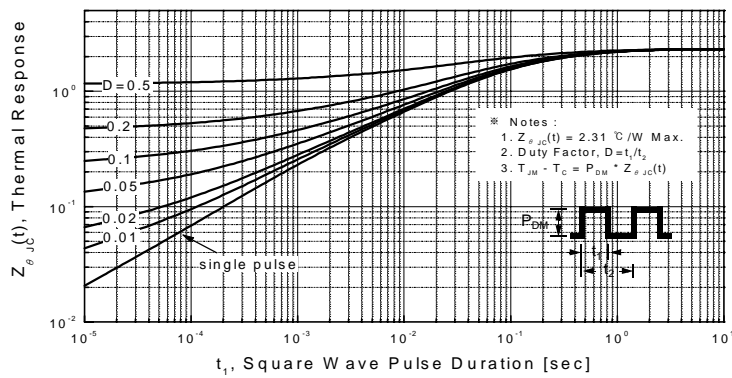
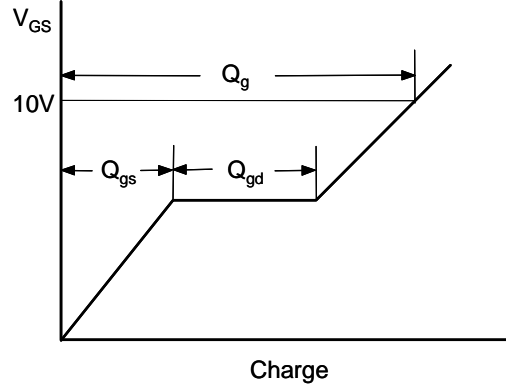
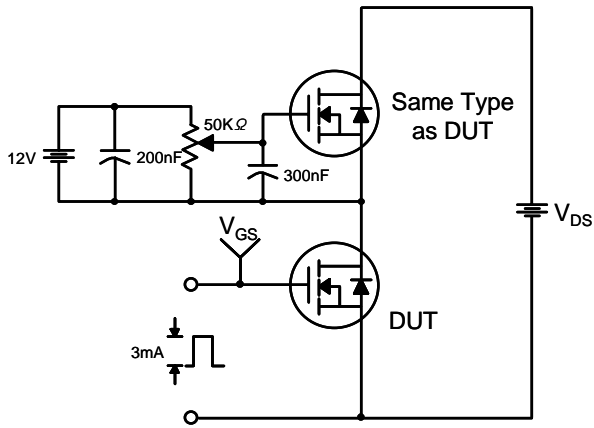
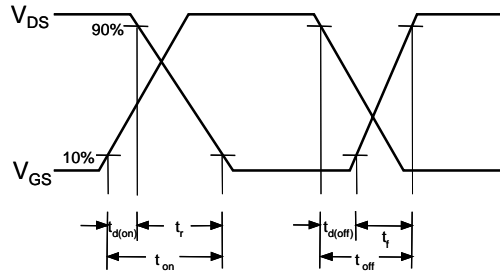
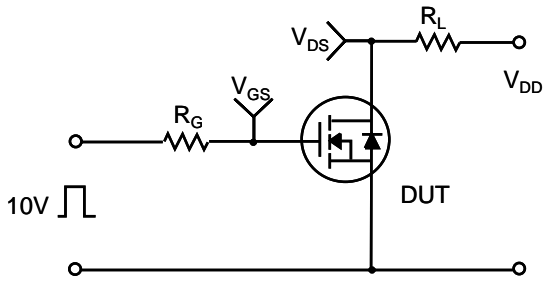


Figure 11. Transient Thermal Response Curve

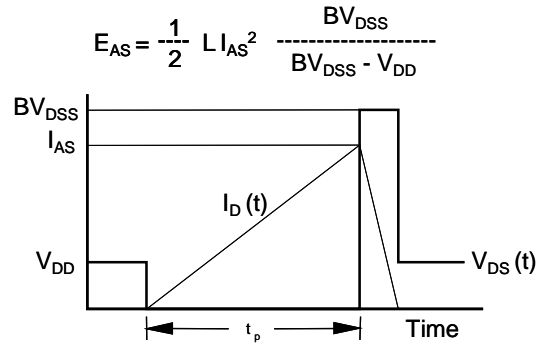
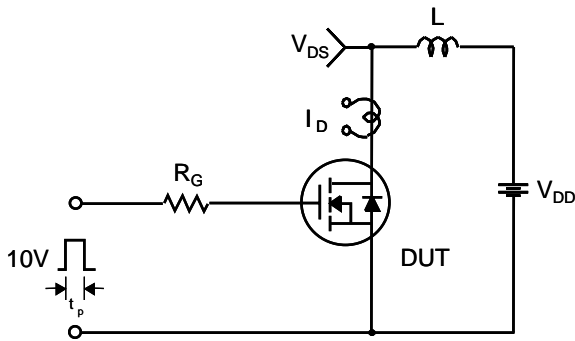
Gate Charge Test Circuit & Waveform



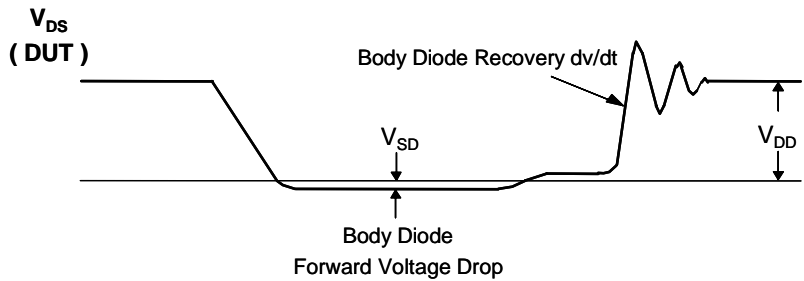
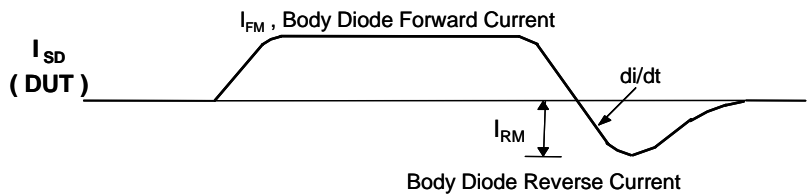
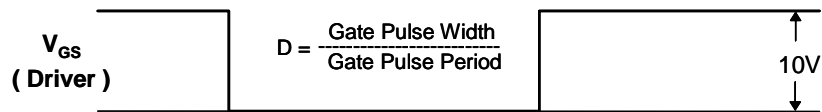
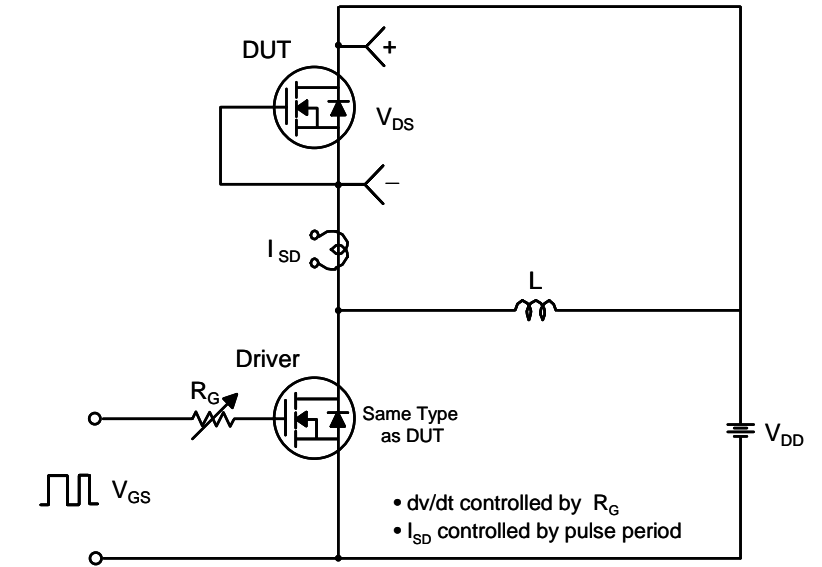
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

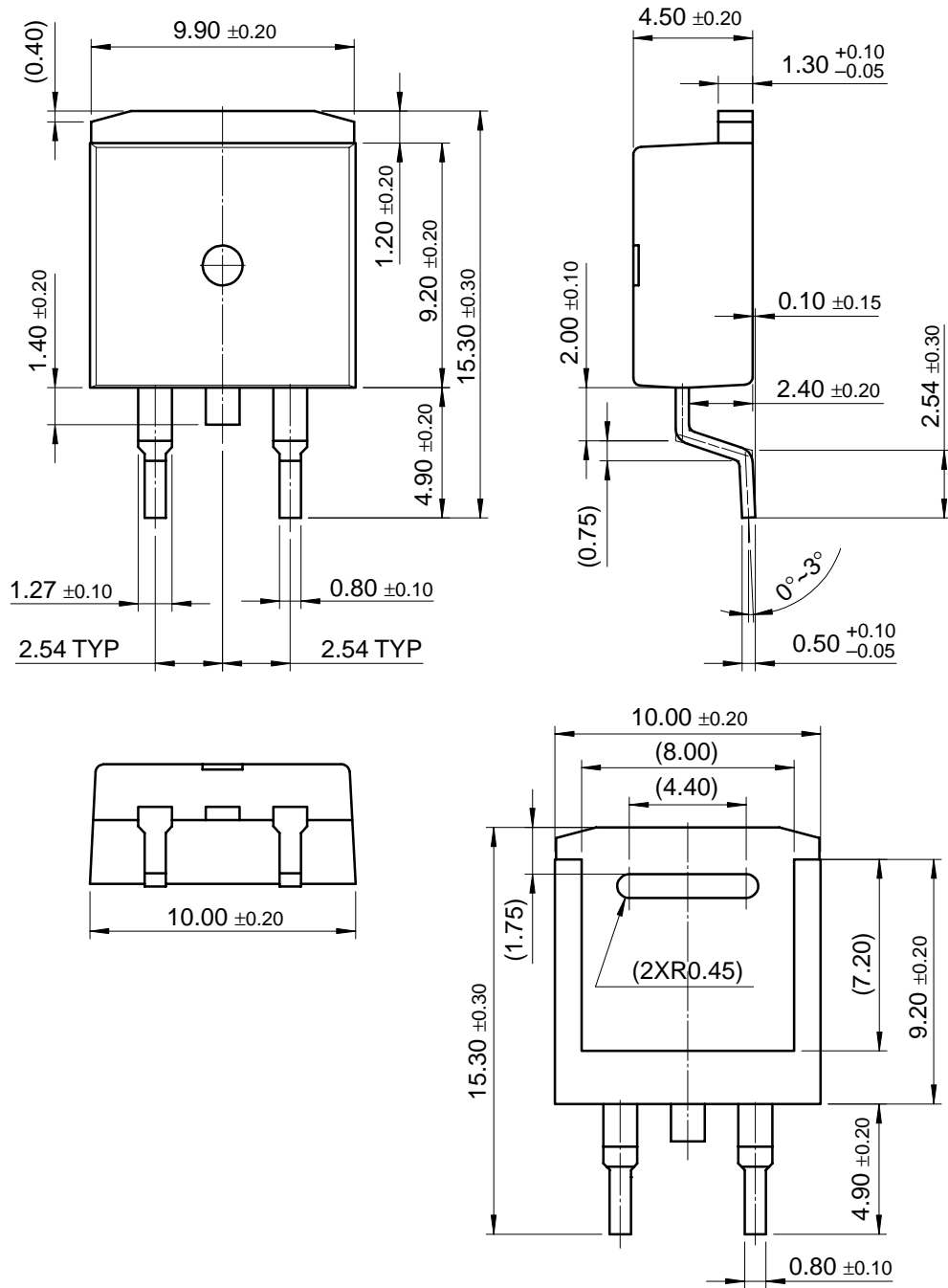


Peak Diode Recovery dv/dt Test Circuit & Waveforms



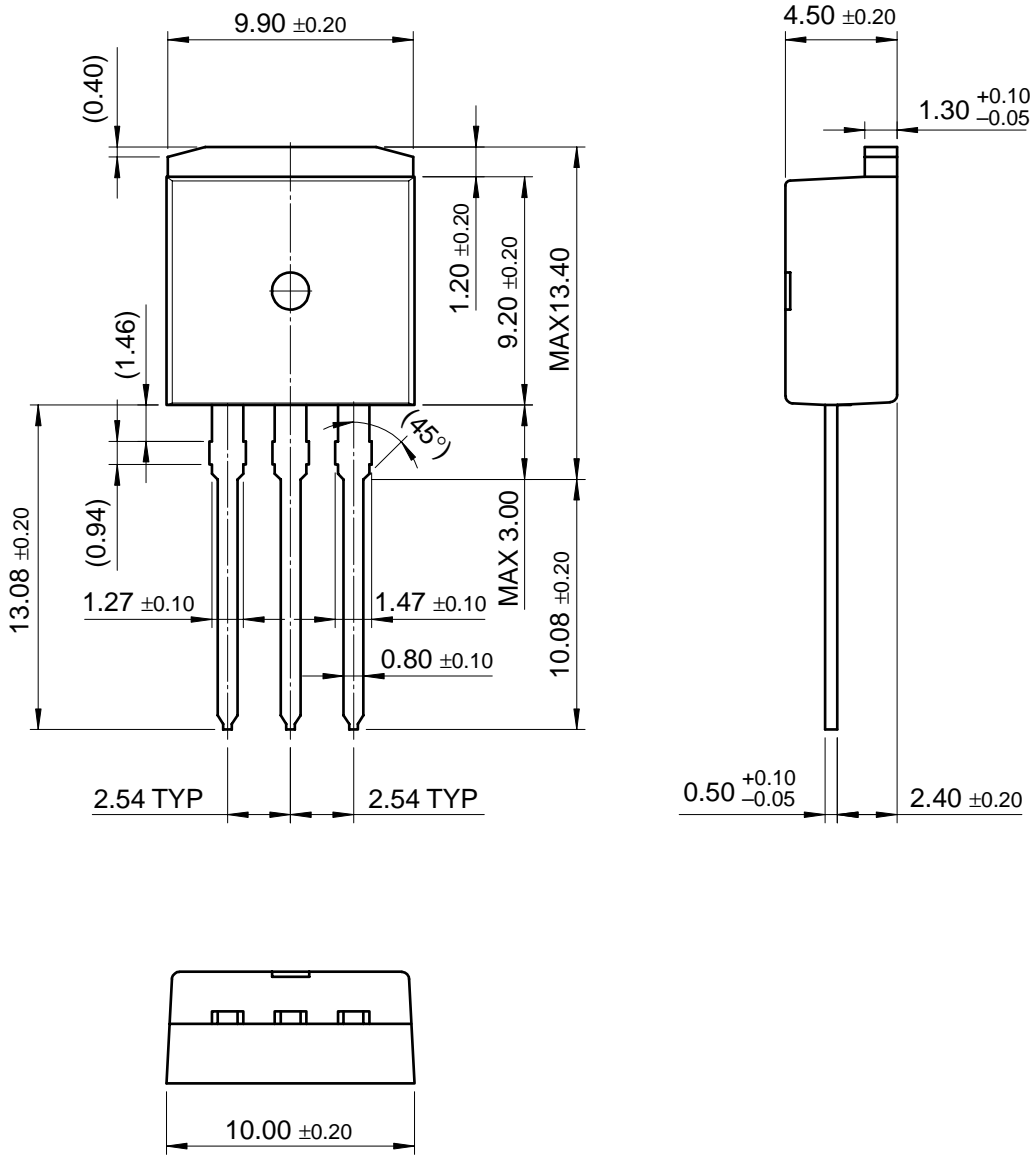
Package Dimensions

D²PAK



Package Dimensions (Continued)

I²PAK



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^x ™	FAST ^r ™	QFET™	VCX™
Bottomless™	GlobalOptoisolator™	QS™	
CoolFET™	GTO™	QT Optoelectronics™	
CROSSVOLT™	HiSeC™	Quiet Series™	
DOME™	ISOPLANAR™	SuperSOT™-3	
E ² CMOS™	MICROWIRE™	SuperSOT™-6	
EnSigna™	OPTOLOGIC™	SuperSOT™-8	
FACT™	OPTOPLANAR™	SyncFET™	
FACT Quiet Series™	POP™	TinyLogic™	
FAST®	PowerTrench®	UHC™	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR INTERNATIONAL.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we strictly control the quality of products and services. Welcome your RFQ to

Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.